

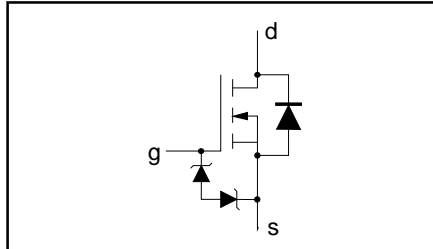
**TrenchMOS™ transistor
Logic level FET**

PHP65N06LT, PHB65N06LT

FEATURES

- 'Trench' technology
- Very low on-state resistance
- Fast switching
- Stable off-state characteristics
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

| |
|--|
| $V_{DSS} = 55\text{ V}$ |
| $I_D = 63\text{ A}$ |
| $R_{DS(ON)} \leq 18\text{ m}\Omega (V_{GS} = 5\text{ V})$ |
| $R_{DS(ON)} \leq 16\text{ m}\Omega (V_{GS} = 10\text{ V})$ |

GENERAL DESCRIPTION

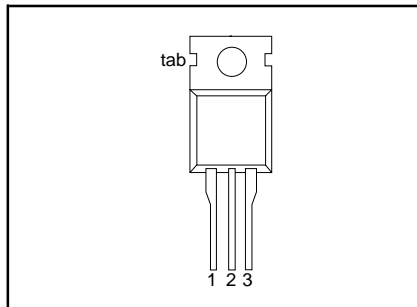
N-channel enhancement mode, logic level, field-effect power transistor in a plastic envelope using 'trench' technology. The device has very low on-state resistance. It is intended for use in dc to dc converters and general purpose switching applications.

The PHP65N06LT is supplied in the SOT78 (TO220AB) conventional leaded package.
The PHB65N06LT is supplied in the SOT404 surface mounting package.

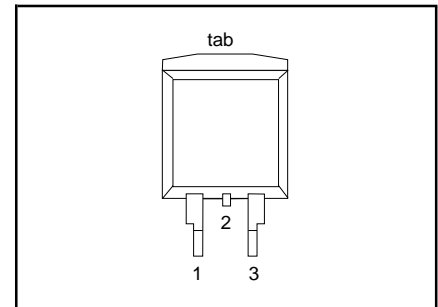
PINNING

| PIN | DESCRIPTION |
|-----|--------------------|
| 1 | gate |
| 2 | drain ¹ |
| 3 | source |
| tab | drain |

SOT78 (TO220AB)



SOT404



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|----------------|--|--|------|----------|------------------|
| V_{DSS} | Drain-source voltage | $T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$ | - | 55 | V |
| V_{DGR} | Drain-gate voltage | $T_j = 25\text{ }^\circ\text{C}$ to $175\text{ }^\circ\text{C}$; $R_{GS} = 20\text{ k}\Omega$ | - | 55 | V |
| V_{GS} | Gate-source voltage | | - | ± 13 | V |
| I_D | Continuous drain current | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 63 | A |
| | | $T_{mb} = 100\text{ }^\circ\text{C}$ | - | 44 | A |
| I_{DM} | Pulsed drain current | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 240 | A |
| P_D | Total power dissipation | $T_{mb} = 25\text{ }^\circ\text{C}$ | - | 150 | W |
| T_j, T_{stg} | Operating junction and storage temperature | | - 55 | 175 | $^\circ\text{C}$ |

¹ It is not possible to make connection to pin 2 of the SOT404 package.

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THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|--|--|----------|--------|------------|
| $R_{th\ j-mb}$ | Thermal resistance junction to mounting base | | - | 1.0 | K/W |
| $R_{th\ j-a}$ | Thermal resistance junction to ambient | SOT78 package, in free air SOT404 package, pcb mounted, minimum footprint | 60 50 | - - | K/W K/W |

ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------|---|--|------|------|------|
| V_C | Electrostatic discharge capacitor voltage, all pins | Human body model (100 pF, 1.5 k Ω) | - | 2 | kV |

ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------|----------------------------------|--|-----------------|----------|-----------------|--|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA};$ $T_j = -55^\circ\text{C}$ | 55 50 | - - | - - | V V |
| $V_{(BR)GSS}$ | Gate-source breakdown voltage | $I_G = \pm 1\text{ mA};$ | 10 | - | - | V |
| $V_{GS(TO)}$ | Gate threshold voltage | $V_{DS} = V_{GS}; I_D = 1\text{ mA}$ $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$ | 1.0 0.5 - | 1.5 - | 2.0 - 2.3 | V V V |
| $R_{DS(ON)}$ | Drain-source on-state resistance | $V_{GS} = 5\text{ V}; I_D = 25\text{ A}$ $V_{GS} = 10\text{ V}; I_D = 25\text{ A}$ $T_j = 175^\circ\text{C}$ | - - - | 15 13 | 18 16 38 | m Ω m Ω m Ω |
| g_{fs} | Forward transconductance | $V_{DS} = 25\text{ V}; I_D = 25\text{ A}$ | 25 | 52 | - | S |
| I_{GSS} | Gate source leakage current | $V_{GS} = \pm 5\text{ V}; V_{DS} = 0\text{ V}$ $T_j = 175^\circ\text{C}$ | - | 0.02 | 1 | μA μA |
| I_{DSS} | Zero gate voltage drain current | $V_{DS} = 55\text{ V}; V_{GS} = 0\text{ V};$ $T_j = 175^\circ\text{C}$ | - | 0.05 | 10 | μA μA |
| $Q_{g(tot)}$ | Total gate charge | $I_D = 50\text{ A}; V_{DD} = 44\text{ V}; V_{GS} = 5\text{ V}$ | - | 34 | - | nC |
| Q_{gs} | Gate-source charge | | - | 8 | - | nC |
| Q_{gd} | Gate-drain (Miller) charge | | - | 17 | - | nC |
| t_{don} | Turn-on delay time | $V_{DD} = 30\text{ V}; I_D = 25\text{ A};$ $V_{GS} = 5\text{ V}; R_G = 10\ \Omega$ Resistive load | - | 30 | 45 | ns |
| t_r | Turn-on rise time | | - | 80 | 130 | ns |
| t_{doff} | Turn-off delay time | | - | 100 | 140 | ns |
| t_f | Turn-off fall time | | - | 50 | 75 | ns |
| L_d | Internal drain inductance | Measured from tab to centre of die | - | 3.5 | - | nH |
| L_d | Internal drain inductance | Measured from drain lead to centre of die (SOT78 package only) | - | 4.5 | - | nH |
| L_s | Internal source inductance | Measured from source lead to source bond pad | - | 7.5 | - | nH |
| C_{iss} | Input capacitance | $V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$ | - | 2000 | 2600 | pF |
| C_{oss} | Output capacitance | | - | 390 | 490 | pF |
| C_{rss} | Feedback capacitance | | - | 200 | 290 | pF |

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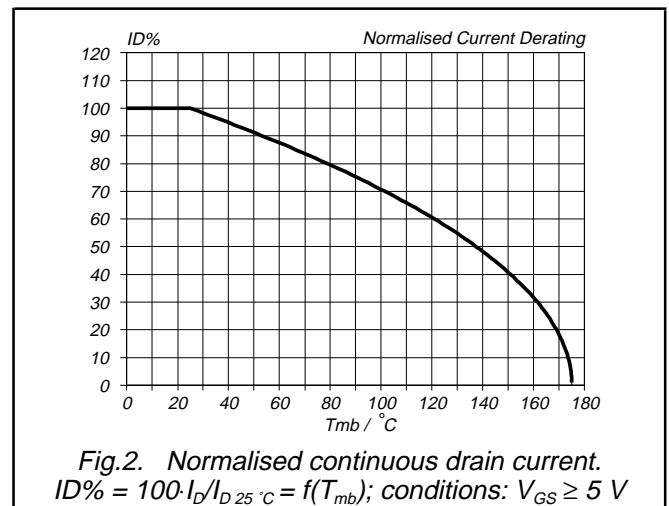
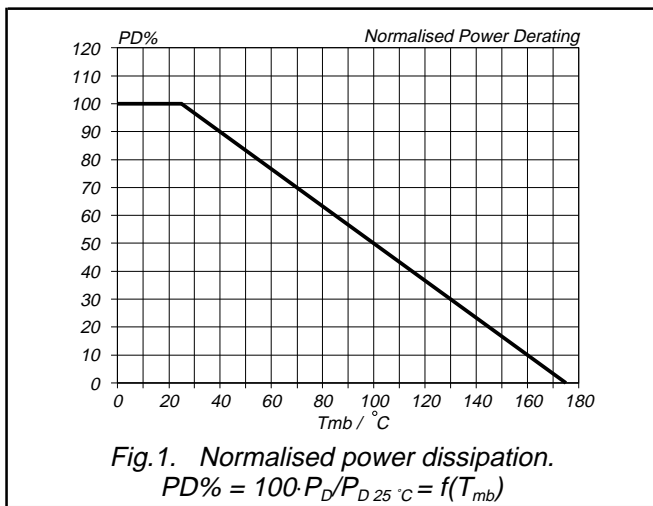
REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_j = 25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------|--|---|------|------|------|------|
| I _S | Continuous source current (body diode) | | - | - | 63 | A |
| I _{SM} | Pulsed source current (body diode) | | - | - | 240 | A |
| V _{SD} | Diode forward voltage | I _F = 25 A; V _{GS} = 0 V | - | 0.95 | 1.2 | V |
| | | I _F = 50 A; V _{GS} = 0 V | - | 1.0 | - | V |
| t _{rr} | Reverse recovery time | I _F = 50 A; -di _F /dt = 100 A/μs; V _{GS} = -10 V; V _R = 30 V | - | 48 | - | ns |
| Q _{rr} | Reverse recovery charge | | - | 0.1 | - | μC |

AVALANCHE LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---|--|------|------|------|
| W _{DSS} | Drain-source non-repetitive unclamped inductive turn-off energy | I _D = 50 A; V _{DD} ≤ 25 V; V _{GS} = 5 V; R _{GS} = 50 Ω; T _{mb} = 25 °C | - | 125 | mJ |



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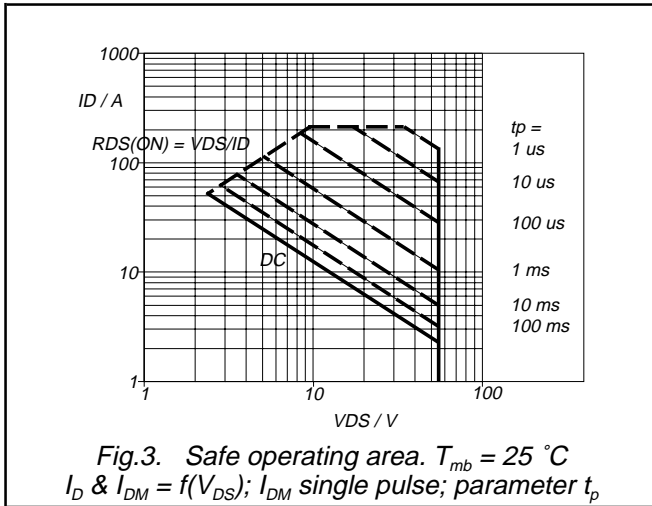


Fig.3. Safe operating area. $T_{mb} = 25^\circ\text{C}$
 I_D & $I_{DM} = f(V_{DS})$; I_{DM} single pulse; parameter t_p

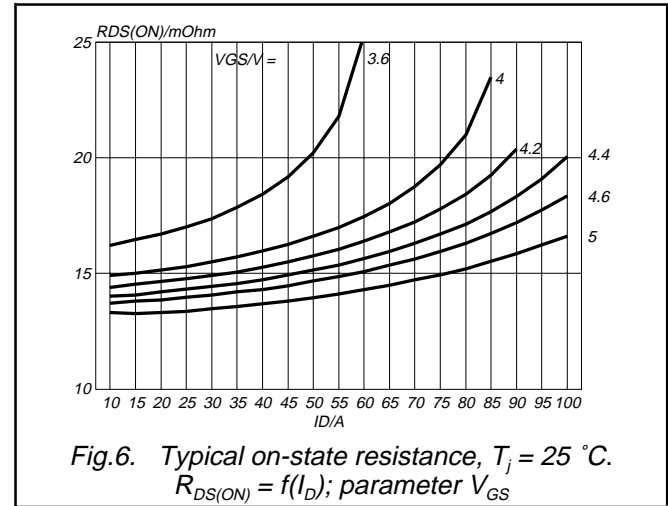


Fig.6. Typical on-state resistance, $T_j = 25^\circ\text{C}$.
 $R_{DS(ON)} = f(I_D)$; parameter V_{GS}

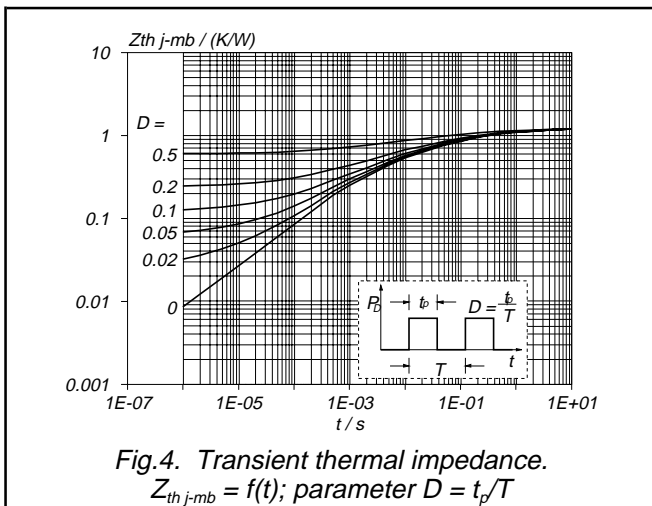


Fig.4. Transient thermal impedance.
 $Z_{th\ j-mb} = f(t)$; parameter $D = t_p/T$

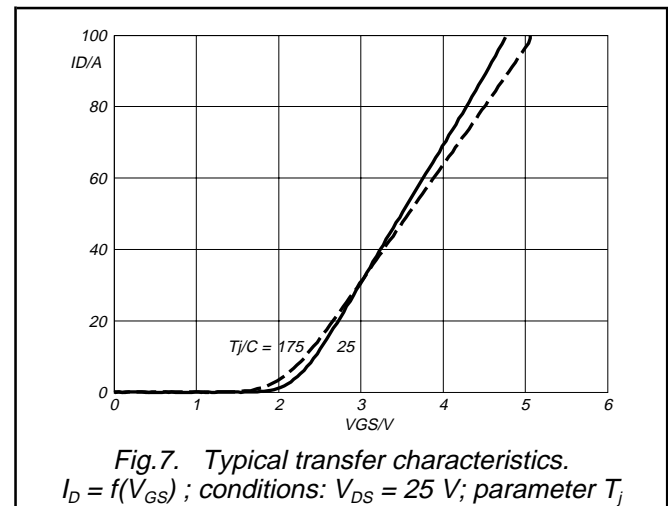


Fig.7. Typical transfer characteristics.
 $I_D = f(V_{GS})$; conditions: $V_{DS} = 25\text{ V}$; parameter T_j

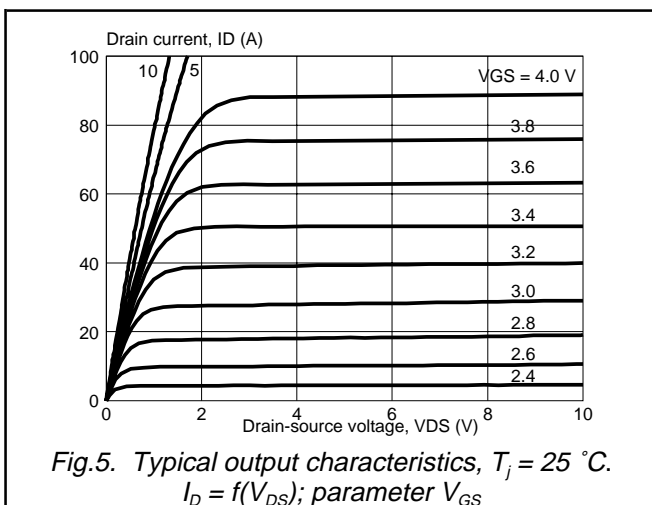


Fig.5. Typical output characteristics, $T_j = 25^\circ\text{C}$.
 $I_D = f(V_{DS})$; parameter V_{GS}

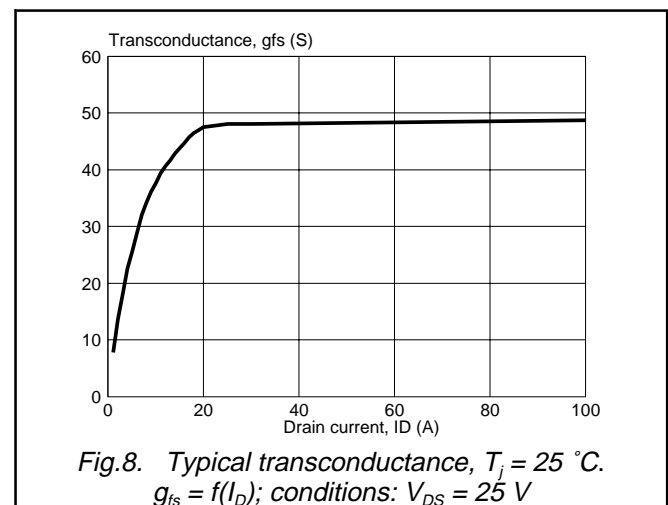
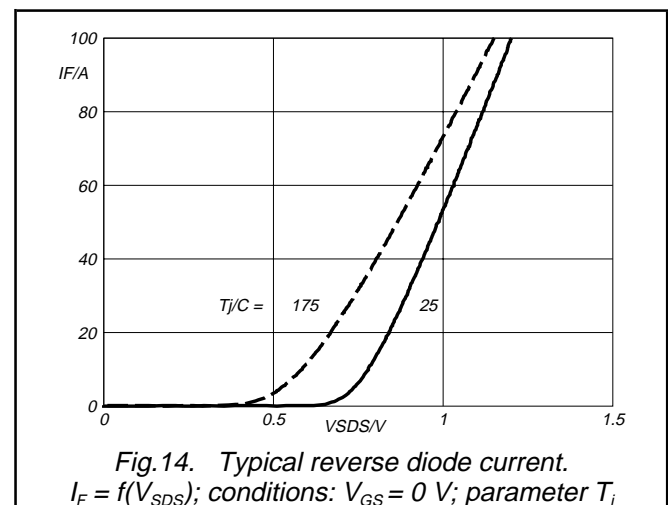
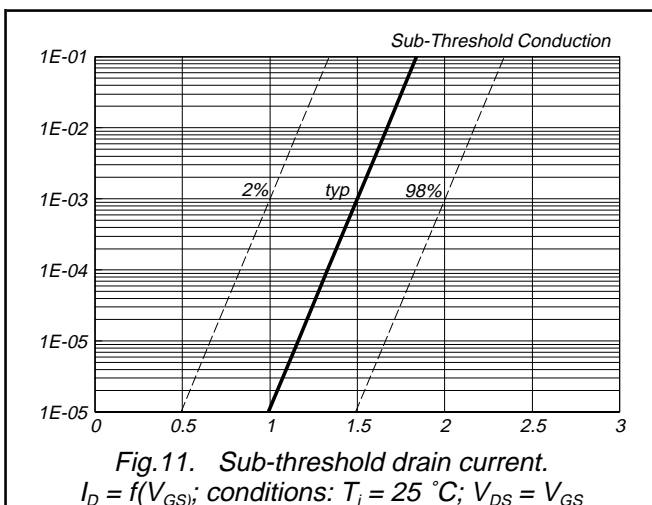
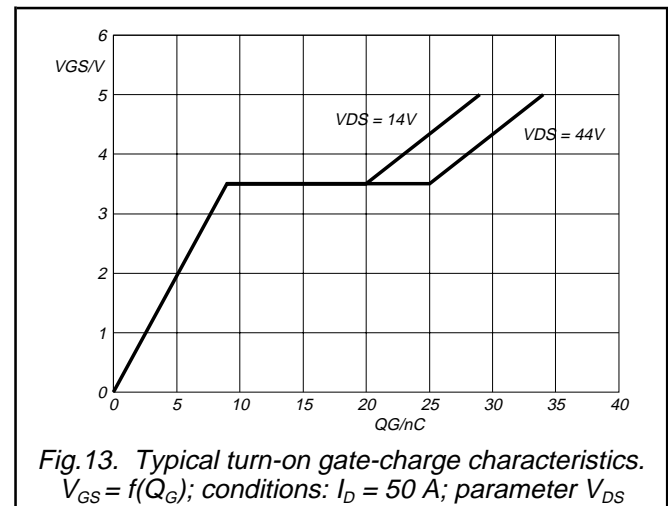
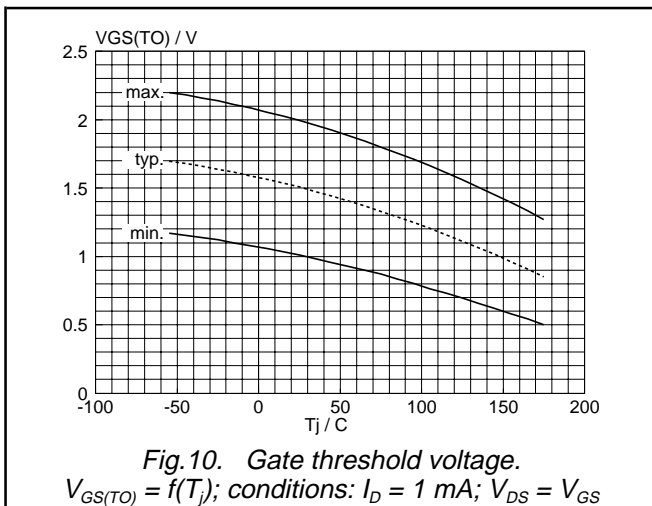
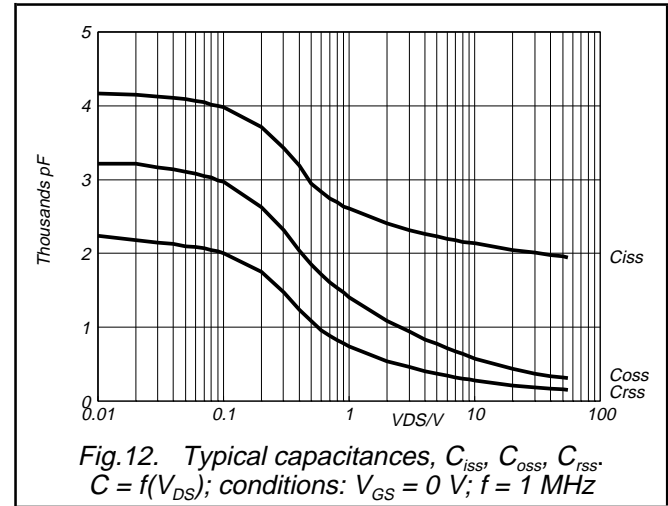
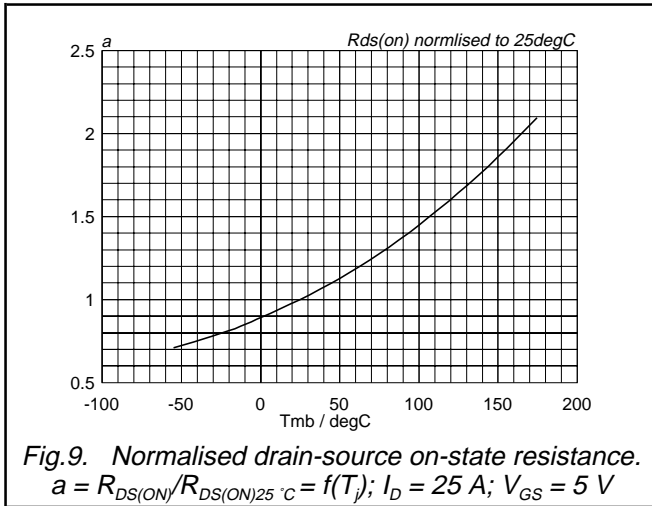


Fig.8. Typical transconductance, $T_j = 25^\circ\text{C}$.
 $g_{fs} = f(I_D)$; conditions: $V_{DS} = 25\text{ V}$

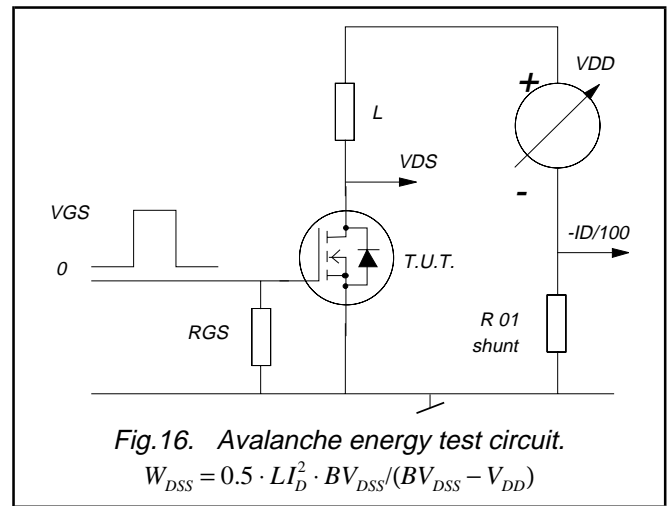
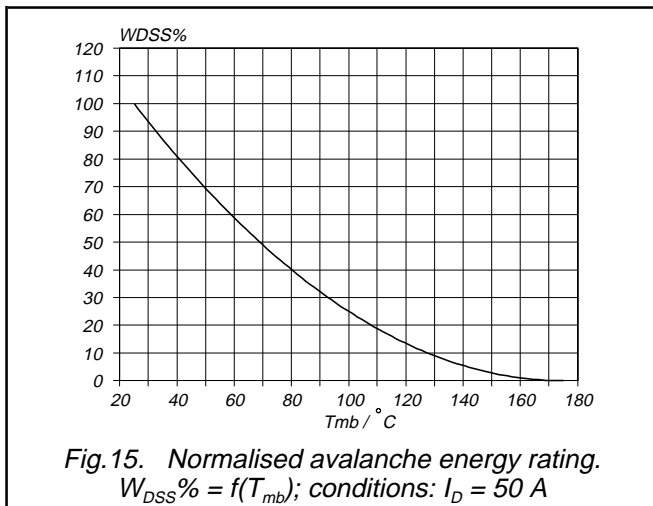
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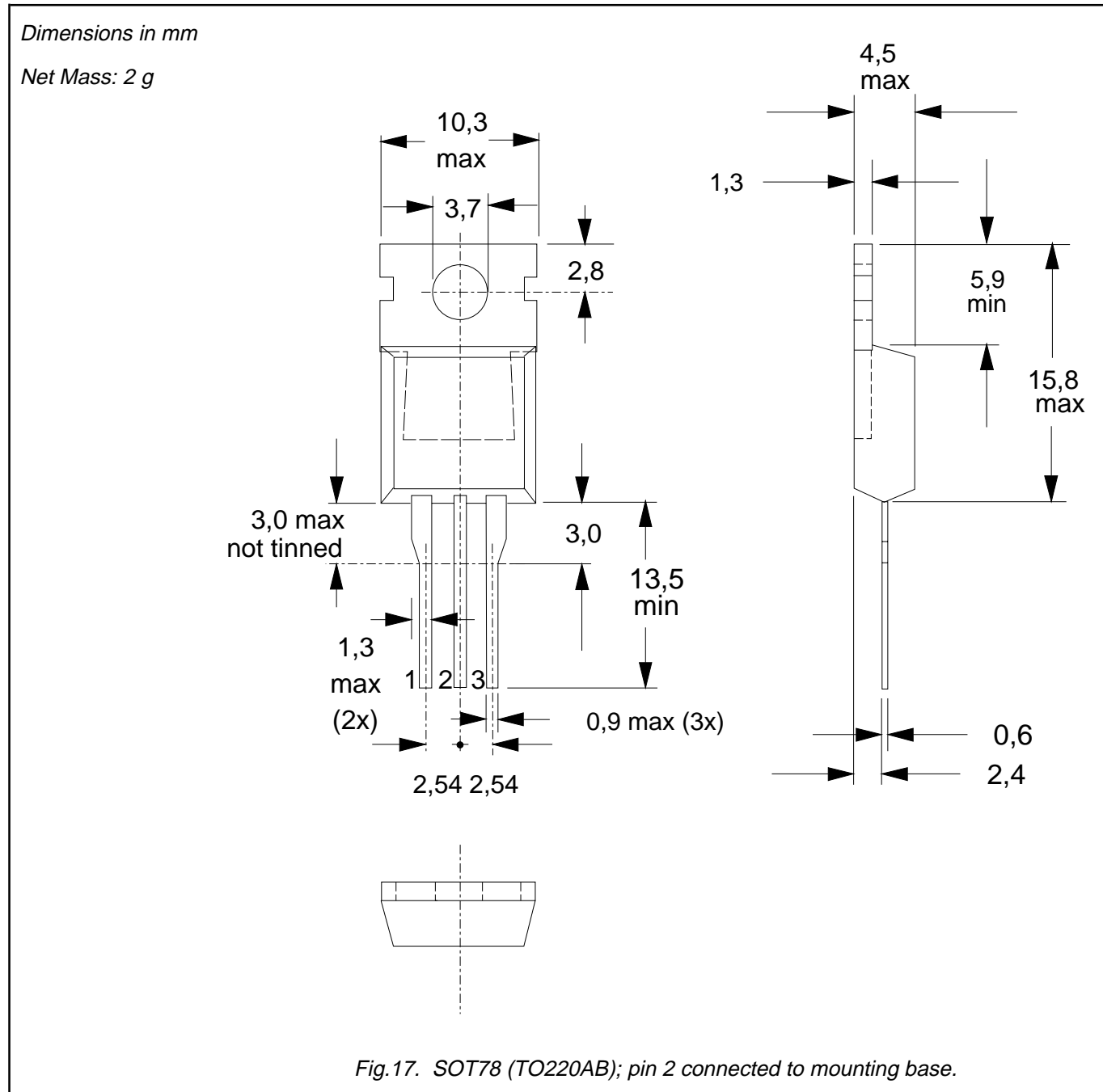
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MECHANICAL DATA



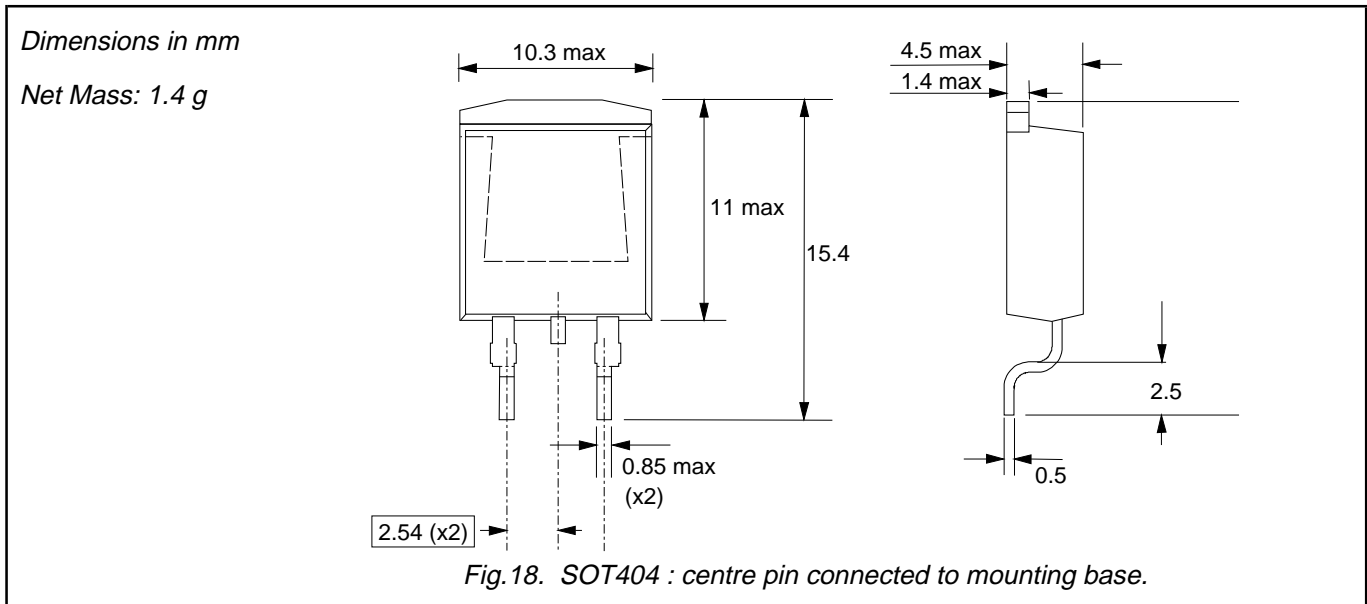
Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Refer to mounting instructions for SOT78 (TO220) envelopes.
3. Epoxy meets UL94 V0 at 1/8".

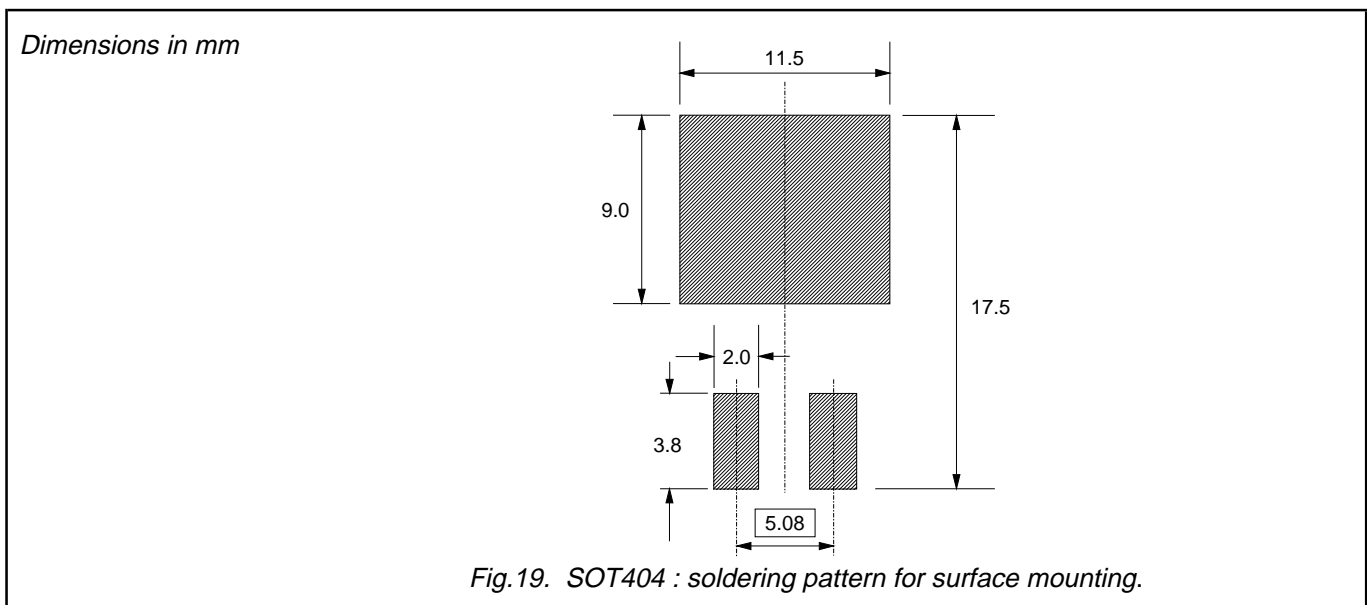
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MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

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2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
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